



International Journal of Engineering and Science Invention

e-ISSN: 2319 – 6734 p-ISSN: 2319 – 6726

CERTIFICATE

It is certify that the paper entitled by “F4-TCNQ Concentration Dependent Capacitance-Voltage (C-V) and Conductivity-Voltage (G/W-V) Characteristics of the Au/P3HT:F4-TCNQ/N-Si (MPS) Schottky Barrier Diodes” has been published in International Journal of Engineering and Science Invention (IJESI).

Your article has been published with following details:

Author's Name: Aslıhançimen, Hüseyinmuzafferşagban, Tuğba Özdemir, Özgetüzün Özmen

Journal Name: International Journal of Engineering and Science Invention (IJESI)

Journal Web: www.ijesi.org

Journal Type: Online & Offline

Review Type: Peer Review Refereed

Publication Year: 2018

Publication Month: July

Vol No.: 07

Issue No.: 07



Editor-In-Chief

International Journal of Engineering and Science Invention (IJESI)

E-mail ID: ijesi@invmails.com

Web: www.ijesi.org

UGC Approval Serial Number: 2573 & UGC Journal Number: 43302